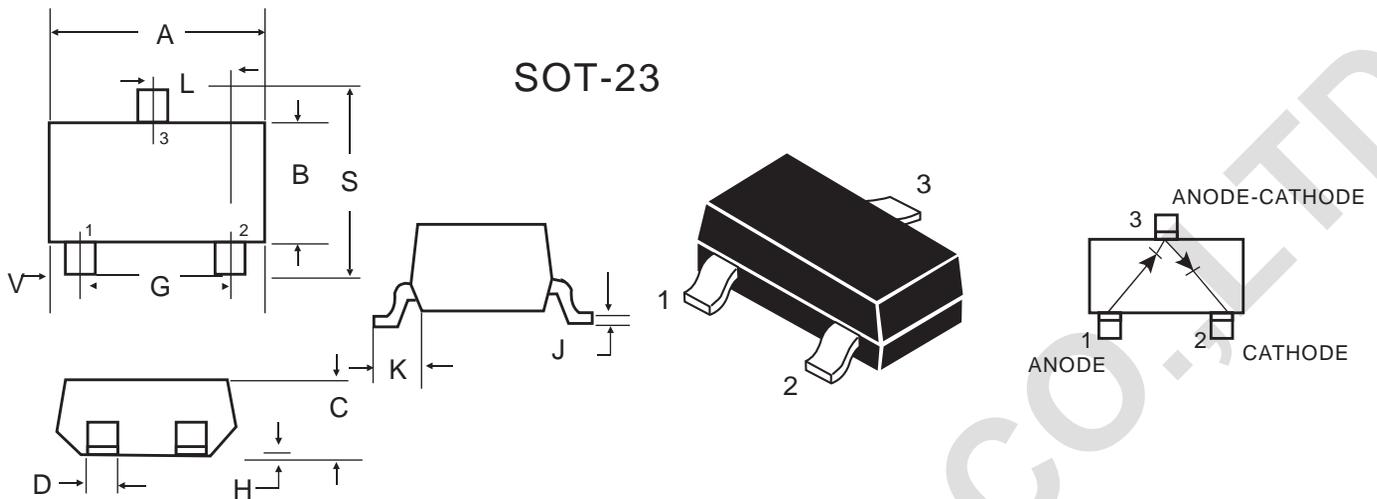


MONOLITHIC DUAL SWITCHING DIODE



Absolute Maximum Ratings

(Ta=25°C)

Characteristic	Symbol	Rating	Unit
Reverse Voltage	VR	50	Vdc
Peak Reverse Voltage	VRM	75	Vdc
Peak Forward Current	IFM	300	mAdc
Average Rectified Current	IO	100	mAdc
Total Device Dissipation FR-5 Board(Note) Derate above 25°C	P _D	225	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C

Electrical Characteristics

(Ta=25°C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Reverse Breakdown Voltage(IR=100uAdc)	V(BR)	75			Vdc
Reverse Voltage Leakage Current (VR=50Vdc)	IR		0.1		nAdc
Diode Capacitance(VR=0 f=1.0MHz)	C _T		4.0		PF
Forward Voltage (IF=10mAdc)	VF		1.0		Vdc
(IF=50mAdc)			1.0		
(IF=50mAdc)			1.2		
Reverse Recovery Time(IF=IR=10mAdc)	T _{rr}		4.0		nS

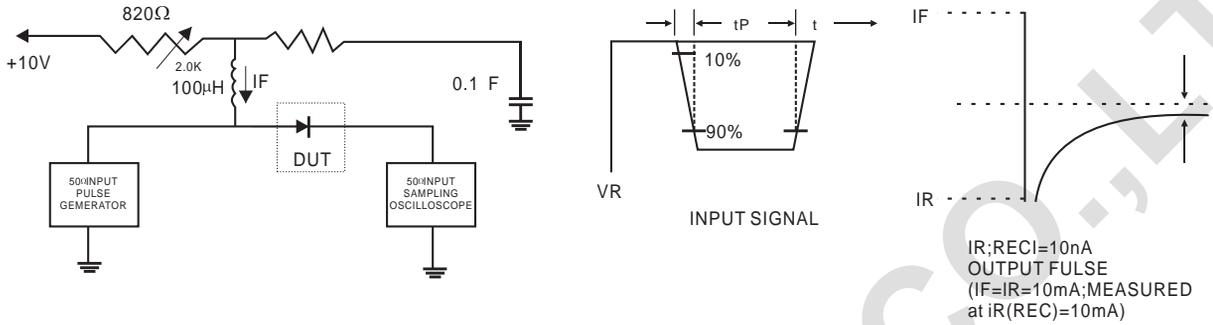
Note:FR-5=1.0X0.75X0.062in

DVICE MARKING:

MMBD2838LT1=A4

MONOLITHIC DUAL SWITCHING DIODE

MMBD2837LT1 MMBD2837LT1



- Notes. 1. A 2.0KΩ Variable resistor adjusted for a Forward Current (IF) of 1C nA
 2. Input pulse is adjusted so IR(peak) is equal to 10 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH CATHODE

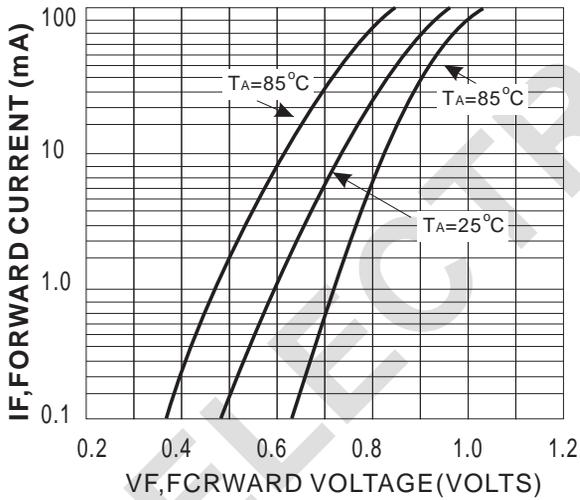


Figure 2 . Forward Voltage

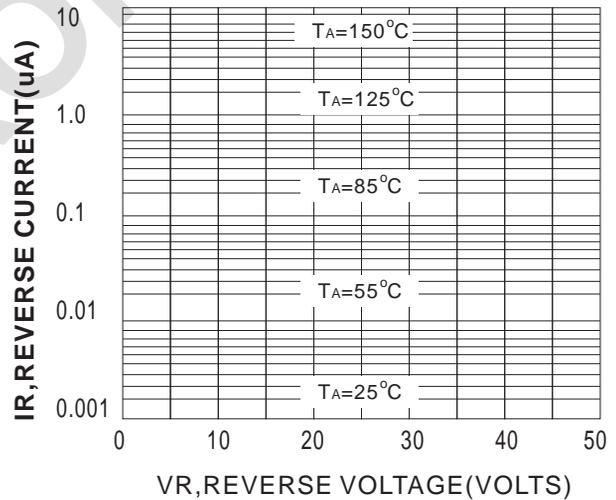


Figure 3 . Leakage Current

